DISCRETE SEMICONDUCTORS

DATA SHEET

PDTC144E series NPN resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

Product specification Supersedes data of 2004 Mar 23 2004 Aug 17





NPN resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

PDTC144E series

FEATURES

- Built-in bias resistors
- · Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

APPLICATIONS

- · General purpose switching and amplification
- · Inverter and interface circuits
- · Circuit driver.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V _{CEO}	collector-emitter voltage	_	50	V
Io	output current (DC)	_	100	mA
R1	bias resistor	47	_	kΩ
R2	bias resistor	47	_	kΩ

DESCRIPTION

NPN resistor-equipped transistor (see "Simplified outline, symbol and pinning" for package details).

PRODUCT OVERVIEW

TYPE NUMBER	PAC	KAGE	MARKING CODE	DAID COMPLEMENT	
I TPE NUMBER	PHILIPS	EIAJ	MARKING CODE	PNP COMPLEMENT	
PDTC144EE	SOT416	SC-75	08	PDTA144EE	
PDTC144EEF	SOT490	SC-89	08	PDTA144EEF	
PDTC144EK	SOT346	SC-59	08	PDTA144EK	
PDTC144EM	SOT883	SC-101	E7	PDTA144EM	
PDTC144ES	SOT54 (TO-92)	SC-43	TC144E	PDTA144ES	
PDTC144ET	SOT23	_	*08 ⁽¹⁾	PDTA144ET	
PDTC144EU	SOT323	SC-70	*08(1)	PDTA144EU	

Note

^{1. * =} p: Made in Hong Kong.

^{* =} t: Made in Malaysia.

^{* =} W: Made in China.

NPN resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

PDTC144E series

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	CIMPLIFIED OUTLINE AND CYMPOL		PINNING
TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PIN	DESCRIPTION
PDTC144ES		1	base
		2	collector
	R1 R1 R2 R2 R2 R2 R2	3	emitter
PDTC144EE PDTC144EF PDTC144EK PDTC144ET PDTC144EU	3 1 R1 R2 2 Top view MDB269	1 2 3	base emitter collector
PDTC144EM	2 R1 R2 2 bottom view MHC506	1 2 3	base emitter collector

NPN resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

PDTC144E series

ORDERING INFORMATION

TYPE NUMBER		PACKAGE	
I TPE NUMBER	NAME	DESCRIPTION	VERSION
PDTC144EE	_	plastic surface mounted package; 3 leads	SOT416
PDTC144EEF	_	plastic surface mounted package; 3 leads	SOT490
PDTC144EK	_	plastic surface mounted package; 3 leads	SOT346
PDTC144EM	_	leadless ultra small plastic package; 3 solder lands; body $1.0 \times 0.6 \times 0.5 \text{ mm}$	SOT883
PDTC144ES	_	plastic single-ended leaded (through hole) package; 3 leads	SOT54
PDTC144ET	_	plastic surface mounted package; 3 leads	SOT23
PDTC144EU	_	plastic surface mounted package; 3 leads	SOT323

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	50	V
V _{CEO}	collector-emitter voltage	open base	_	50	V
V _{EBO}	emitter-base voltage	open collector	_	10	V
VI	input voltage				
	positive		_	+40	V
	negative		_	-10	V
Io	output current (DC)		_	100	mA
I _{CM}	peak collector current		_	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C			
	SOT54	note 1	_	500	mW
	SOT23	note 1	_	250	mW
	SOT346	note 1	_	250	mW
	SOT323	note 1	_	200	mW
	SOT416	note 1	_	150	mW
	SOT490	notes 1 and 2	_	250	mW
	SOT883	notes 2 and 3	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Notes

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60 μm copper strip line.

NPN resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

PDTC144E series

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	in free air		
	SOT54	note 1	250	K/W
	SOT23	note 1	500	K/W
	SOT346	note 1	500	K/W
	SOT323	note 1	625	K/W
	SOT416	note 1	833	K/W
	SOT490	notes 1 and 2	500	K/W
	SOT883	notes 2 and 3	500	K/W

Notes

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60 μm copper strip line.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	V _{CB} = 50 V; I _E = 0 A	_	_	100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$	_	_	1	μΑ
		$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}; T_{j} = 150 ^{\circ}\text{C}$	_	_	50	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A	_	_	90	μΑ
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 5 \text{ mA}$	80	_	_	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	_	_	150	mV
$V_{i(off)}$	input-off voltage	$I_C = 100 \mu\text{A}; V_{CE} = 5 \text{V}$	_	1.2	0.8	٧
V _{i(on)}	input-on voltage	$I_C = 2 \text{ mA}; V_{CE} = 0.3 \text{ V}$	3	1.6	_	٧
R1	input resistor		33	47	61	kΩ
R2 R1	resistor ratio		0.8	1	1.2	
C _c	collector capacitance	I _E = i _e = 0 A; V _{CB} = 10 V; f = 1 MHz	_	_	2.5	pF

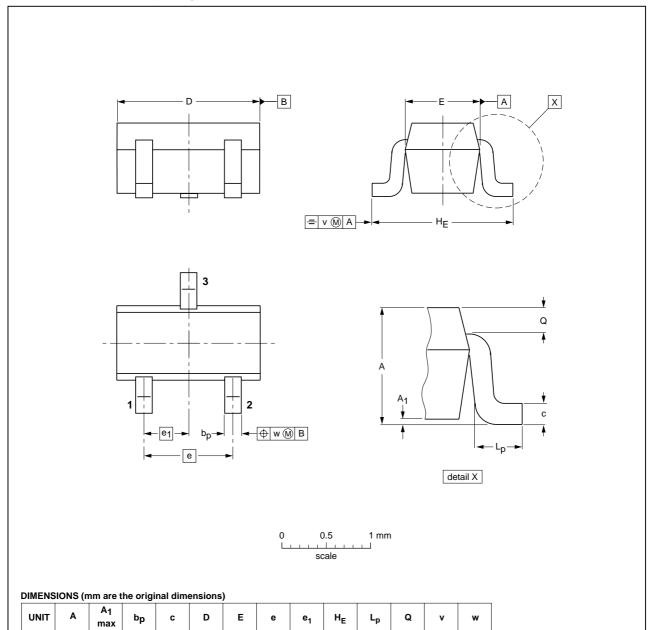
NPN resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

PDTC144E series

PACKAGE OUTLINES

Plastic surface mounted package; 3 leads

SOT416



OUTLINE		REFER	REFERENCES			ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT416			SC-75			97-02-28	

1.75

1.45

1

0.5

0.45

0.23

0.2

0.2

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0.30

0.15

0.95

0.1

0.25

0.10

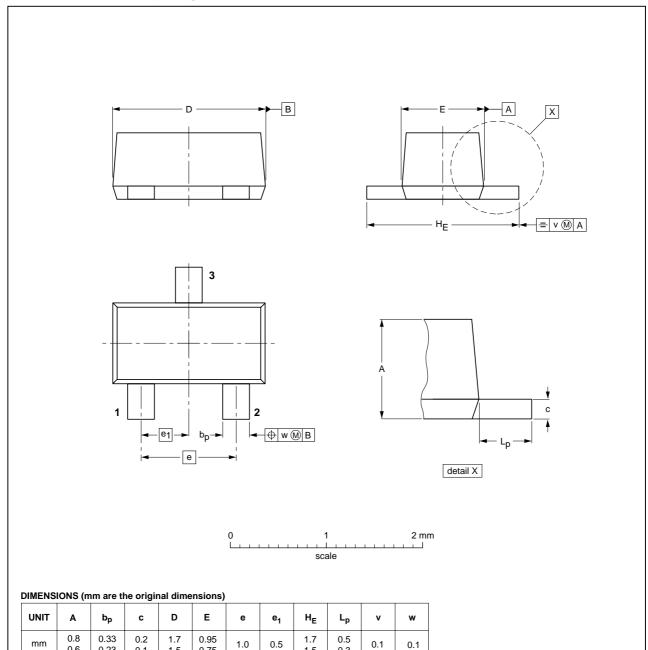
1.8

NPN resistor-equipped transistors; $R1 = 47 \text{ k}\Omega$, $R2 = 47 \text{ k}\Omega$

PDTC144E series

Plastic surface mounted package; 3 leads

SOT490



OUTLINE		REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT490			SC-89			98-10-23	

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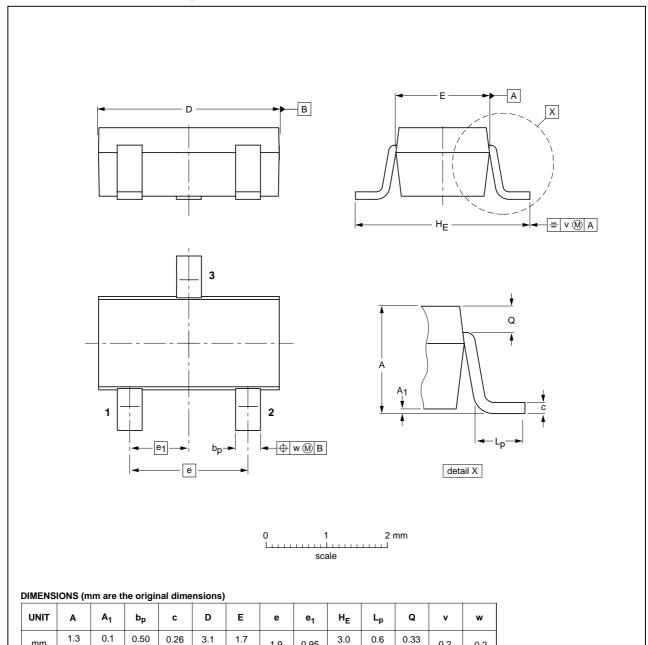
0.6

NPN resistor-equipped transistors; $R1 = 47 \text{ k}\Omega$, $R2 = 47 \text{ k}\Omega$

PDTC144E series

Plastic surface mounted package; 3 leads

SOT346



OUTLINE		REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT346		TO-236	SC-59			98-07-17	

0.95

0.2

0.2

1.9

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1.0

0.013

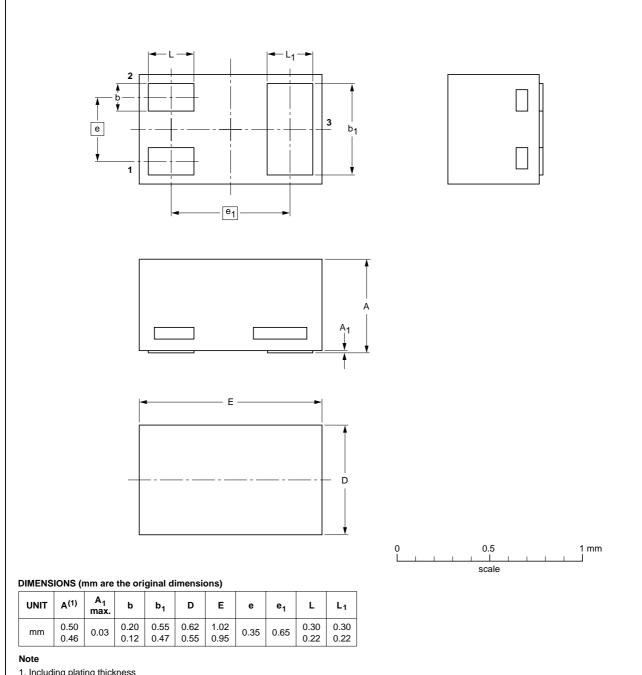
0.35

NPN resistor-equipped transistors; $R1 = 47 \text{ k}\Omega$, $R2 = 47 \text{ k}\Omega$

PDTC144E series

Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

SOT883



1. Including plating thickness

OUTLINE		REFER	RENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT883			SC-101		03-02-05 03-04-03	

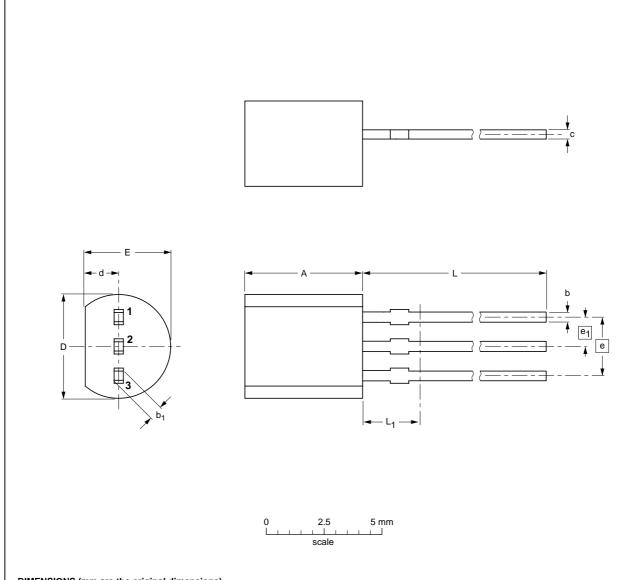
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NPN resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

PDTC144E series

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



DIMENSIONS (mm are the original dimensions)

UNIT	Α	b	b ₁	С	D	d	E	е	e ₁	L	L ₁ ⁽¹⁾ max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

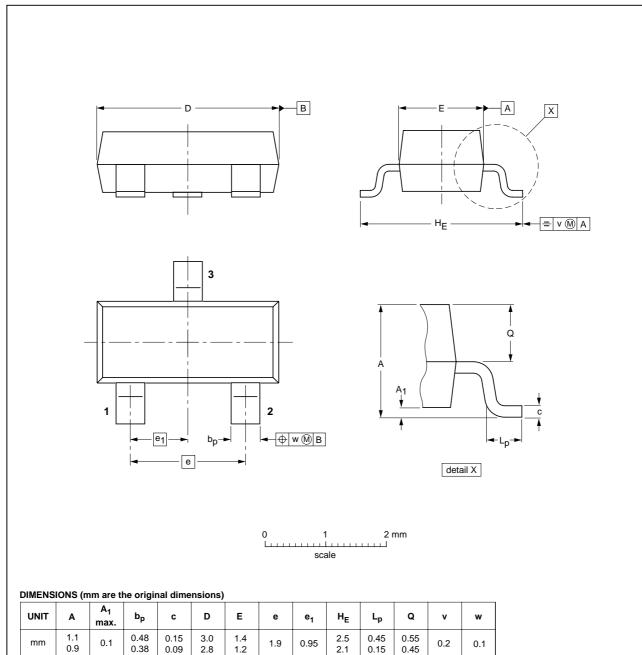
OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT54		TO-92	SC-43A			97-02-28 04-06-28

NPN resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

PDTC144E series

Plastic surface mounted package; 3 leads

SOT23



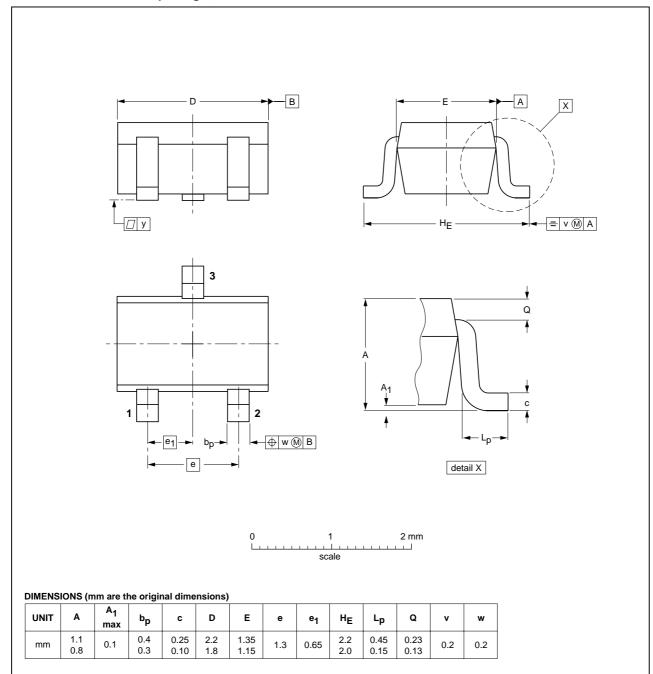
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VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT23		TO-236AB				-97-02-28 99-09-13

NPN resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

PDTC144E series

Plastic surface mounted package; 3 leads

SOT323



OUTLINE		REFERENCES				EUROPEAN	ISSUE DATE
	VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
	SOT323			SC-70			97-02-28

NPN resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

PDTC144E series

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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